

Title (en)

METHOD AND APPARATUS FOR MANUFACTURING A FUNCTIONAL LAYER ON A SEMICONDUCTOR DEVICE

Title (de)

VERFAHREN UND ANORDNUNG ZUM HERSTELLEN EINER FUNKTIONSSCHICHT AUF EINEM HALBLEITERBAUELEMENT

Title (fr)

PROCÉDÉ ET DISPOSITIF DE FABRICATION D'UNE COUCHE FONCTIONELLE SUR UN DISPOSITIF SEMI-CONDUCTEUR

Publication

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Application

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Priority

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Abstract (en)

[origin: WO2010023225A1] The invention relates to a method for producing at least one functional layer on at least one region of a surface of a semiconductor component by applying a liquid to at least the one region, wherein the functional layer has a layer thickness d1 and the liquid required for forming the functional layer having the thickness d1 has a layer thickness d2. In order that functional layers having a desired thin and uniform thickness are produced in a reproducible manner, it is proposed that the liquid is applied to the at least one region of the surface in excess with a layer thickness d3 where $d3 > d2$ and that subsequently, either with the semiconductor component moved in translational fashion or with the semiconductor component arranged in stationary fashion, excess liquid is removed from the surface in a contactless manner to an extent such that the liquid layer has the thickness d2 or approximately the thickness d2.

IPC 8 full level

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Citation (search report)

See references of WO 2010023225A1

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